

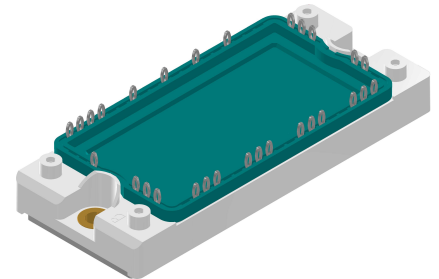
High Voltage Thyristor Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 2200\text{ V}$	$V_{CES} = 1700\text{ V}$
$I_{DAV} = 120\text{ A}$	$I_{C25} = 113\text{ A}$
$I_{FSM} = 500\text{ A}$	$V_{CE(sat)} = 2.5\text{ V}$

3~ Rectifier Bridge, half-controlled (high-side) + Brake Unit

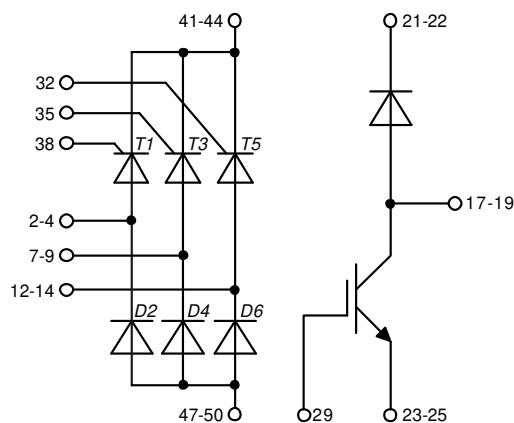
Part number

MCNA120UI2200PED



Backside: isolated

 E72873



Features / Advantages:

- Thyristor/Standard Rectifier for line frequency
- Planar passivated chips
- Long-term stability
- Low forward voltage drop
- Copper base plate with Direct Copper Bonded Al₂O₃-ceramic
- Improved temperature and power cycling

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

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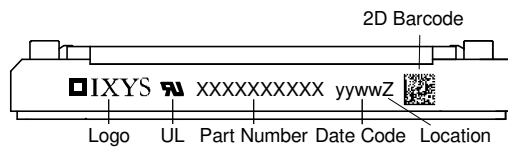
Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2200	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 2200 V$	$T_{VJ} = 25^{\circ}C$		50	μA	
		$V_{R/D} = 2200 V$	$T_{VJ} = 125^{\circ}C$		10	mA	
V_T	forward voltage drop	$I_T = 40 A$	$T_{VJ} = 25^{\circ}C$		1.33	V	
		$I_T = 120 A$			2.05	V	
		$I_T = 40 A$	$T_{VJ} = 125^{\circ}C$		1.36	V	
		$I_T = 120 A$			2.38	V	
I_{DAV}	bridge output current	$T_C = 80^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 150^{\circ}C$		120	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.83	V	
r_T	slope resistance				13.6	m Ω	
R_{thJC}	thermal resistance junction to case				0.65	K/W	
R_{thCH}	thermal resistance case to heatsink			0.1		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		190	W	
I_{TSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		500	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		540	A	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		425	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		460	A	
I^2t	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		1.25	kA ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		1.22	kA ² s	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		905	A ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		880	A ² s	
C_J	junction capacitance	$V_R = 700 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		13	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 Hz$ repetitive, $I_T = 120 A$			150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V = 2/3 V_{DRM}$ non-repet., $I_T = 40 A$			500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = 2/3 V_{DRM}$ $R_{GK} = \infty; method 1 (linear voltage rise)$	$T_{VJ} = 150^{\circ}C$		1000	V/ μs	
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.4	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		70	mA	
			$T_{VJ} = -40^{\circ}C$		150	mA	
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V	
I_{GD}	gate non-trigger current				5	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		150	mA	
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$					
I_H	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA	
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2	μs	
t_q	turn-off time	$V_R = 100 V; I_T = 40 A; V = 2/3 V_{DRM}$ $di/dt = 10 A/\mu s dv/dt = 20 V/\mu s t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$	500		μs	



Brake IGBT + Diode				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1700	V			
V_{GES}	max. DC gate voltage				± 20	V			
V_{GEM}	max. transient gate emitter voltage				± 30	V			
I_{C25}	collector current	$T_C = 25^{\circ}C$			113	A			
I_{C80}		$T_C = 80^{\circ}C$			80	A			
P_{tot}	total power dissipation	$T_C = 25^{\circ}C$			445	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}$			2.5	V			
					3	V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3\text{ mA}; V_{GE} = V_{CE}$	5.2	5.8	6.4	V			
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.6	mA			
					5	mA			
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			400	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 900\text{ V}; V_{GE} = 15\text{ V}; I_C = 75\text{ A}$		850		nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 900\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 18\ \Omega$							
t_r	current rise time						$T_{VJ} = 125^{\circ}C$	270	ns
$t_{d(off)}$	turn-off delay time						100	ns	
t_f	current fall time						700	ns	
E_{on}	turn-on energy per pulse						430	ns	
E_{off}	turn-off energy per pulse						34	mJ	
		17.5	mJ						
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 18\ \Omega$							
I_{CM}		$V_{CEK} = 1700\text{ V}$			150	A			
SCSOA	short circuit safe operating area	$V_{CEK} = 1700\text{ V}$							
t_{SC}	short circuit duration	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15$			10	μs			
I_{SC}	short circuit current	$R_G = 18\ \Omega$; non-repetitive		280		A			
R_{thJC}	thermal resistance junction to case				0.28	K/W			
R_{thCH}	thermal resistance case to heatsink				0.1	K/W			
Brake Diode									
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}C$			1700	V			
I_{F25}	forward current	$T_C = 25^{\circ}C$			75	A			
I_{F80}		$T_C = 80^{\circ}C$			50	A			
V_F	forward voltage	$I_F = 60\text{ A}$			2.45	V			
					2.20	V			
I_R	reverse current	$V_R = V_{RRM}$			0.1	mA			
					1	mA			
Q_{rr}	reverse recovery charge	$V_R = 900\text{ V}$ $-di_F/dt = 600\text{ A}/\mu s$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$							
I_{RM}	max. reverse recovery current						$T_{VJ} = 125^{\circ}C$	20	μC
t_{rr}	reverse recovery time						46	A	
E_{rec}	reverse recovery energy						1300	ns	
					10.5	mJ			
R_{thJC}	thermal resistance junction to case				0.65	K/W			
R_{thCH}	thermal resistance case to heatsink				0.1	K/W			



Package E2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			40	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				176		g
M_D	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 3000			V V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				



Part description

- M = Module
- C = Thyristor (SCR)
- N = High Voltage Thyristor
- A = (>= 2000V)
- 120 = Current Rating [A]
- UI = 3- Rectifier Bridge, half-controlled (high-side) + Brake Unit
- 2200 = Reverse Voltage [V]
- P = PressFit-Pin
- ED = E2-Pack
- = Hyphen
- PC = Phase Change Material

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCNA120UI2200PED	MCNA120UI2200PED	Blister	28	521435
Alternative	MCNA120UI2200PED-PC	MCNA120UI2200PED	Blister	28	521428

Equivalent Circuits for Simulation

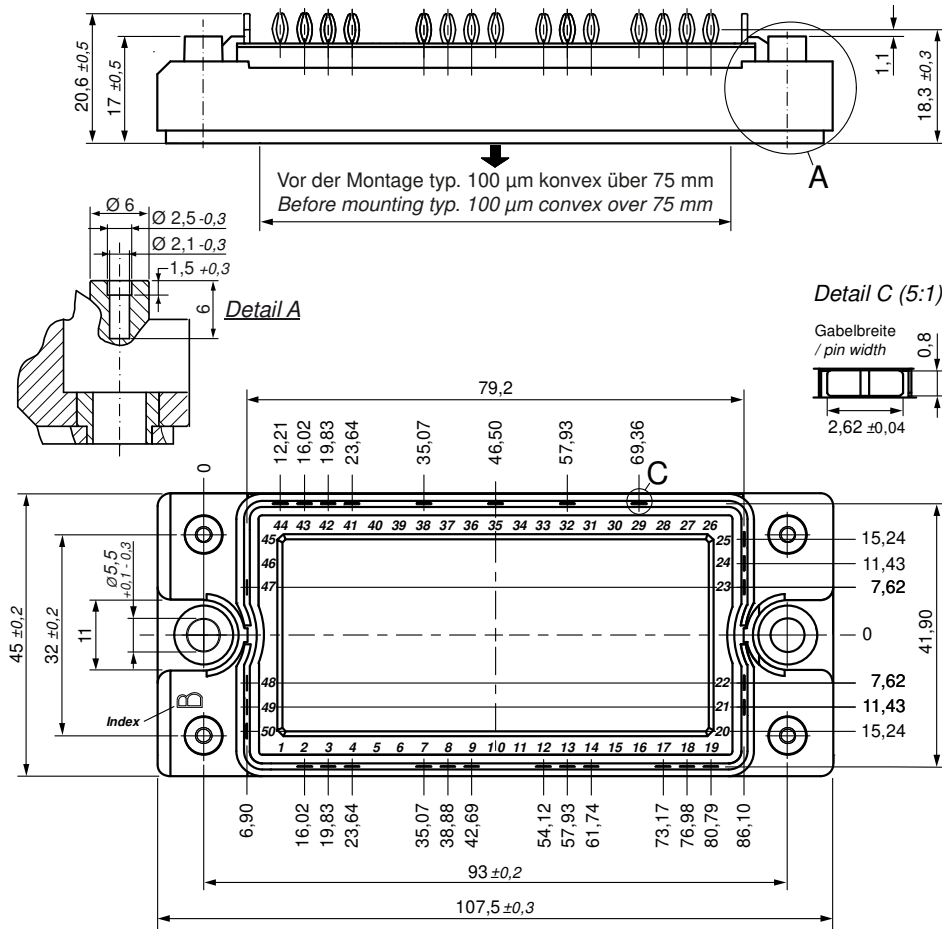
* on die level

$T_{VJ} = 150^{\circ}C$

		Thyristor	Brake IGBT +	Brake Diode	
V_0	threshold voltage	0.83	1.17	1.34	V
R_0	slope resistance *	10.5	25	15.2	mΩ



Outlines E2-Pack

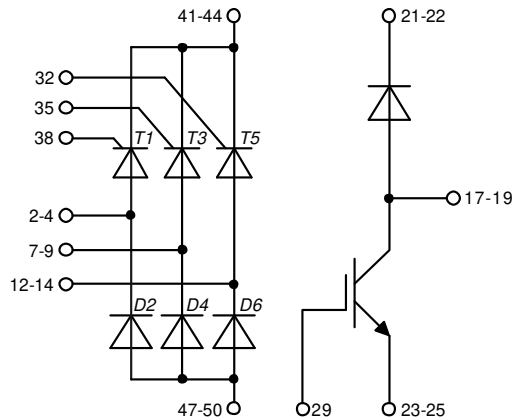


Bemerkung / Note:

- Nicht tolerierte Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern: $\oplus 0.1$
- Bohrlochdurchmesser / Diameter of drill: **Ø 2.35 mm**
- Endlochdurchmesser / Diameter of plated holes: **Ø 2.14 - 2.29 mm** (Cu thickness in via typ. 50 µm)
- Beschichtung / Plating: **chem. Sn max. 15 µm**
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of 7 mm/s: **typ. 90 N**
- Weitere Angaben / Further information: www.ixys.com **Application note IXAN0077**
- Montageanleitung / Mounting instruction: www.ixys.com **Application note IXAN0024**

Detail A: PCB-Montage / Mounting on PCB^L

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)^L
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)^L
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



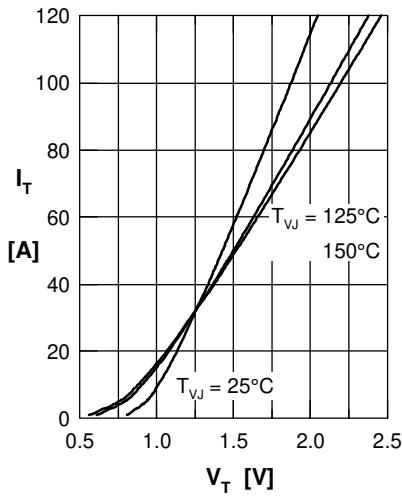
Thyristor


Fig. 1 Forward characteristics

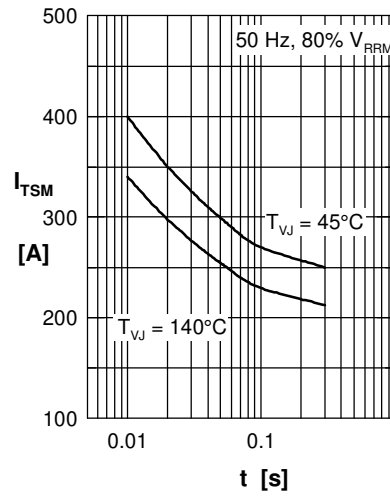
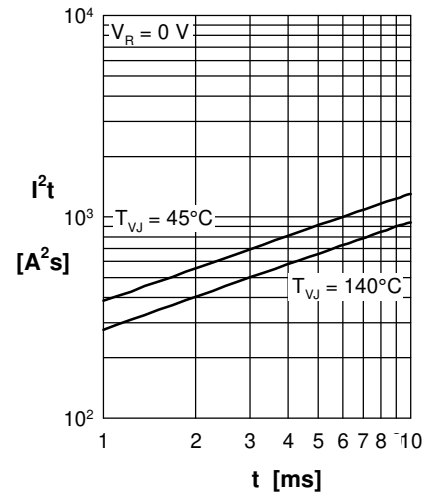
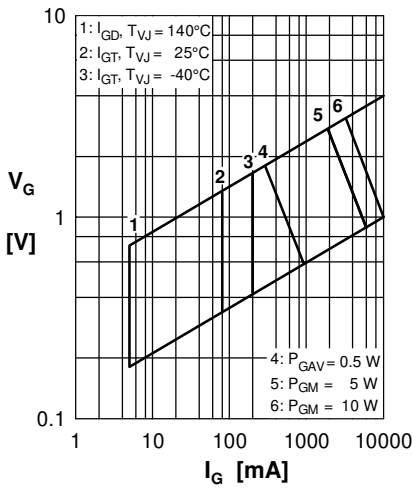

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

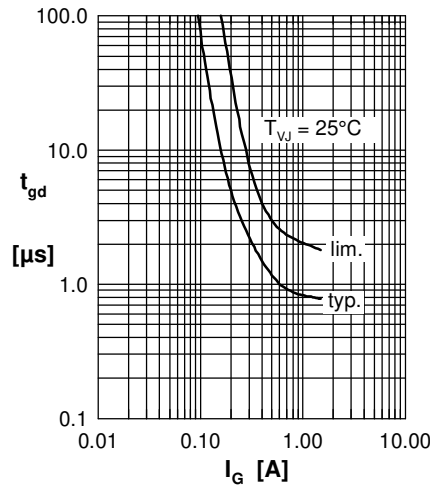
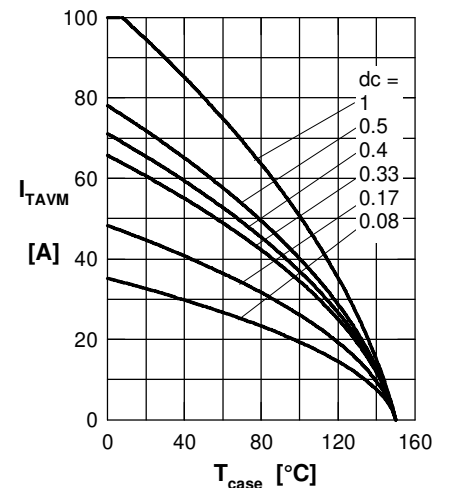

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

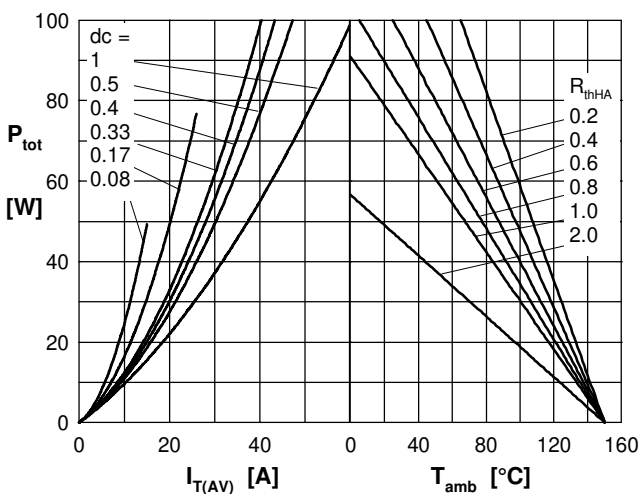
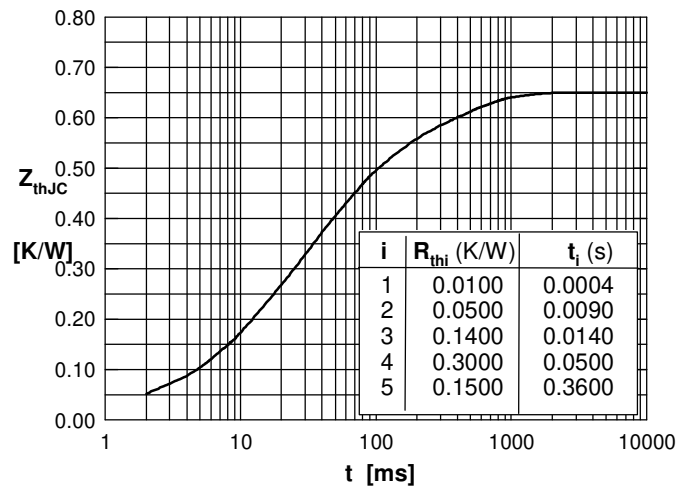

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case

Brake IGBT + Diode

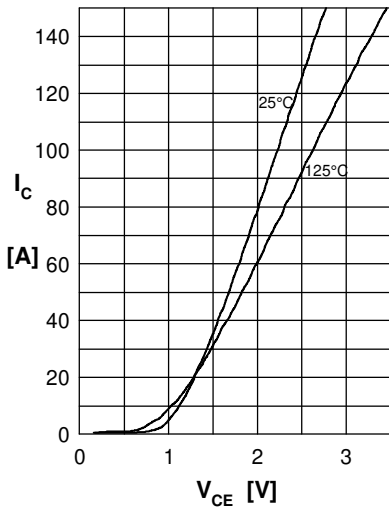


Fig.1 Output characteristics IGBT



Fig.2 Typ. output characteristics IGBT

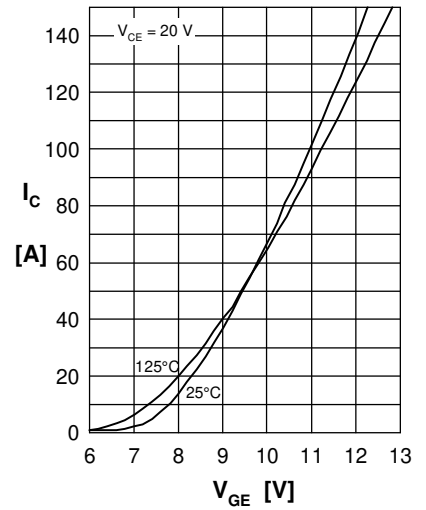


Fig.3 Typ. transfer charact. IGBT

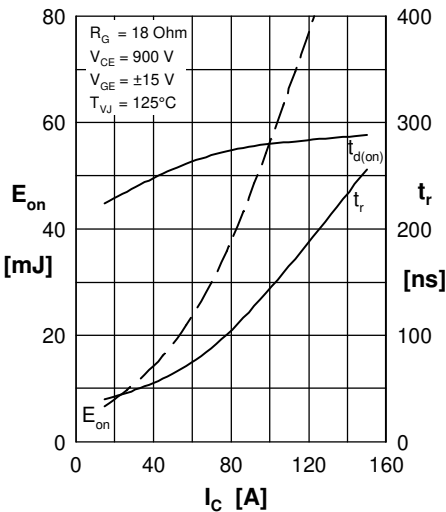


Fig.4 Typ. turn-on energy & switch. times vs. collector current

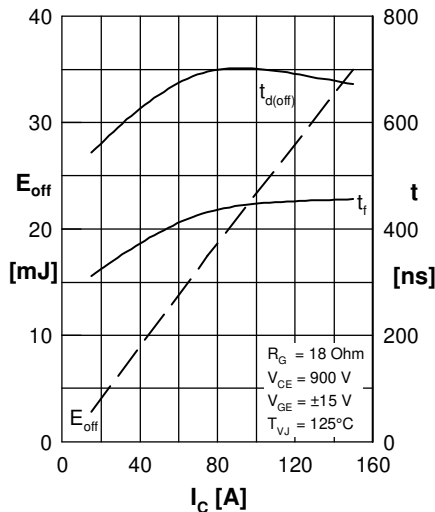


Fig.5 Typ. turn-off energy & switch. times vs. collector current

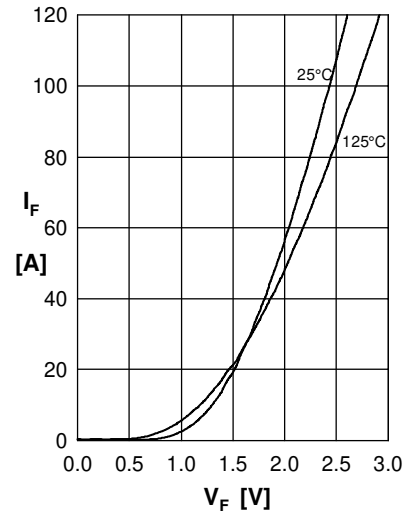


Fig.6 Typ. forward characteristics Diode

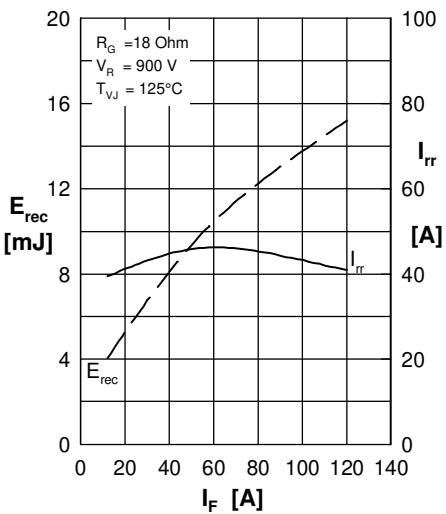


Fig.7 Typ. reverse recovery characteristics Diode

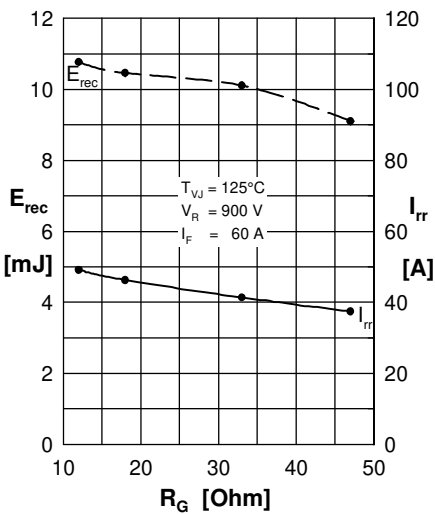


Fig.8 reverse recovery characteristics Diode

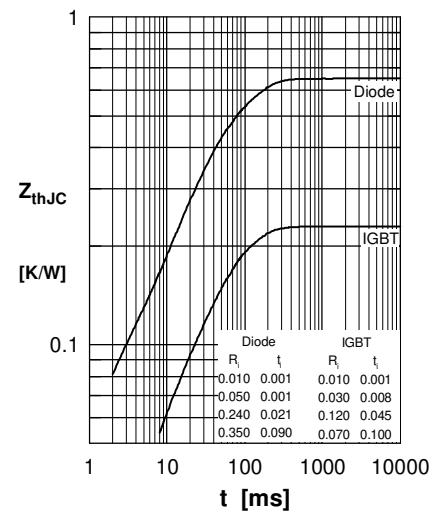


Fig.9 Transient thermal resistance junction to case